

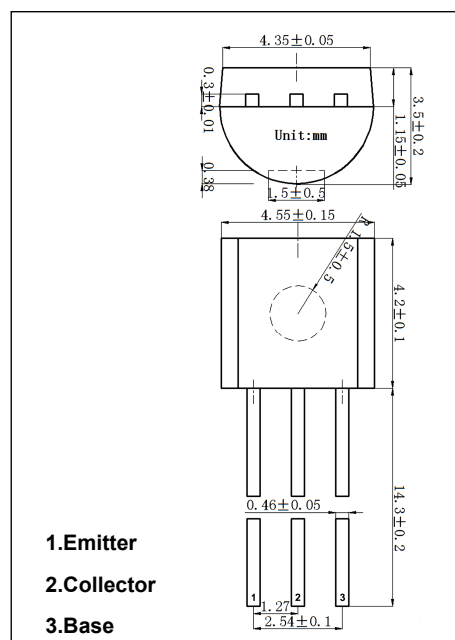
TO-92 Plastic-Encapsulate Transistors

ALJB772P01 PNP Transistors

Features

- Low speed switching

Marking: ALJB772P01



Maximum Ratings ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector Base Voltage	-40	V
V_{CE0}	Collector Emitter Voltage	-30	V
V_{EB0}	Emitter Base Voltage	-6	V
I_c	Collector Current	-2	A
P_c	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	$^{\circ}\text{C/W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	- 55 to +150	$^{\circ}\text{C}$

Electrical Characteristics ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_c=-100\mu\text{A}, I_E=0$	-40			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_c=-10\text{mA}, I_B=0$	-30			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-100\mu\text{A}, I_C=0$	-6			V
I_{CBO}	Collector cut-off current	$V_{CB}=-40\text{V}, I_E=0$			-1	μA
I_{CEO}	Collector cut-off current	$V_{CE}=-30\text{V}, I_B=0$			-10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-6\text{V}, I_C=0$			-1	μA
$h_{FE(1)}$	DC current gain	$V_{CE}=-5\text{V}, I_C=-1\text{mA}$	60			
$h_{FE(1)}$		$V_{CE}=-2\text{V}, I_C=-1\text{A}$	60		400	
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=-2\text{A}, I_B=-0.2\text{A}$			-0.5	V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C=-2\text{A}, I_B=-0.2\text{A}$			-1.5	V
f_T	Transition frequency	$V_{CE}=-5\text{V}, I_C=-0.1\text{A}, f=10\text{MHz}$	50	80		MHz

Classification OF $h_{FE(1)}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

Typical Characteristics

